

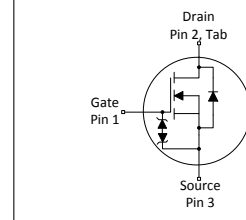
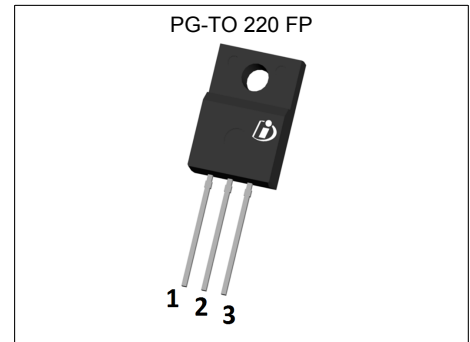
MOSFET

700V CoolMOS™ P7 Power Transistor

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies.

The latest CoolMOS™ P7 is an optimized platform tailored to target cost sensitive applications in consumer markets such as charger, adapter, lighting, TV, etc.

The new series provides all the benefits of a fast switching Superjunction MOSFET, combined with an excellent price/performance ratio and state of the art ease-of-use level. The technology meets highest efficiency standards and supports high power density, enabling customers going towards very slim designs.



Features

- Extremely low losses due to very low FOM $R_{DS(on)} * Q_g$ and $R_{DS(on)} * E_{oss}$
- Excellent thermal behavior
- Integrated ESD protection diode
- Low switching losses (E_{oss})
- Product validation acc. JEDEC Standard

Benefits

- Cost competitive technology
- Lower temperature
- High ESD ruggedness
- Enables efficiency gains at higher switching frequencies
- Enables high power density designs and small form factors



Potential applications

Recommended for Flyback topologies for example used in Chargers, Adapters, Lighting Applications, etc.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

Table 1 Key Performance Parameters

| Parameter | Value | Unit |
|------------------------------|-------|----------|
| $V_{DS} @ T_{j=25^{\circ}C}$ | 700 | V |
| $R_{DS(on),max}$ | 0.6 | Ω |
| $Q_{g,typ}$ | 10.5 | nC |
| $I_{D,pulse}$ | 20.5 | A |
| $E_{oss} @ 400V$ | 1.2 | μJ |
| $V_{(GS)th,typ}$ | 3 | V |
| ESD class (HBM) | 2 | |

| Type / Ordering Code | Package | Marking | Related Links |
|----------------------|---------------------------------|----------|----------------|
| IPAN70R600P7S | PG-TO 220 FullPAK - Narrow Lead | 70S600P7 | see Appendix A |

Table of Contents

| | |
|---|----|
| Description | 1 |
| Maximum ratings | 3 |
| Thermal characteristics | 3 |
| Electrical characteristics | 4 |
| Electrical characteristics diagrams | 6 |
| Test Circuits | 10 |
| Package Outlines | 11 |
| Appendix A | 12 |
| Revision History | 13 |
| Trademarks | 13 |
| Disclaimer | 13 |

1 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|----------------|------------|------|------------|------------------|---|
| | | Min. | Typ. | Max. | | |
| Continuous drain current ¹⁾ | I_D | - | - | 8.5 5.0 | A | $T_C = 20^\circ\text{C}$ $T_C = 100^\circ\text{C}$ |
| Pulsed drain current ²⁾ | $I_{D,pulse}$ | - | - | 20.5 | A | $T_C=25^\circ\text{C}$ |
| Application (Flyback) relevant avalanche current, single pulse ³⁾ | I_{AS} | - | - | 3.2 | A | measured with standard leakage inductance of transformer of $7\mu\text{H}$ |
| MOSFET dv/dt ruggedness | dv/dt | - | - | 100 | V/ns | $V_{DS} = 0 \dots 400\text{V}$ |
| Gate source voltage | V_{GS} | -16 -30 | - | 16 30 | V | static; AC ($f > 1\text{ Hz}$) |
| Power dissipation | P_{tot} | - | - | 24.9 | W | $T_C=25^\circ\text{C}$ |
| Operating and storage temperature | T_j, T_{stg} | -40 | - | 150 | $^\circ\text{C}$ | - |
| Continuous diode forward current | I_S | - | - | 4.5 | A | $T_C=25^\circ\text{C}$ |
| Diode pulse current ²⁾ | $I_{S,pulse}$ | - | - | 20.5 | A | $T_C = 25^\circ\text{C}$ |
| Reverse diode dv/dt ⁴⁾ | dv/dt | - | - | 1 | V/ns | $V_{DS} = 0 \dots 400\text{V}$, $I_{SD} \leq I_S$, $T_j=25^\circ\text{C}$ |
| Maximum diode commutation speed ⁴⁾ | di/dt | - | - | 50 | A/ μs | $V_{DS} = 0 \dots 400\text{V}$, $I_{SD} \leq I_S$, $T_j=25^\circ\text{C}$ |
| Insulation withstand voltage | V_{ISO} | - | - | 2500 | V | V_{rms} , $T_C=25^\circ\text{C}$, $t=1\text{ min}$ |

2 Thermal characteristics

Table 3 Thermal characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|------------|--------|------|------|--------------------|--------------------------------------|
| | | Min. | Typ. | Max. | | |
| Thermal resistance, junction | R_{thJC} | - | - | 5.0 | $^\circ\text{C/W}$ | - |
| Thermal resistance, junction - ambient | R_{thJA} | - | - | 80 | $^\circ\text{C/W}$ | leaded |
| Thermal resistance, junction - ambient for SMD version | R_{thJA} | - | - | - | $^\circ\text{C/W}$ | n.a. |
| Soldering temperature, wavesoldering only allowed at leads | T_{sold} | - | - | 260 | $^\circ\text{C}$ | 1.6 mm (0.063 in.) from case for 10s |

¹⁾ DPAK / IPAK equivalent. Limited by $T_{j,max}$. $T_j = 20^\circ\text{C}$. Maximum duty cycle $D=0.5$

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Proven during verification test. For explanation please read AN - CoolMOS™ 700V P7.

⁴⁾ $V_{DClink}=400\text{V}$; $V_{DS,peak} < V_{(BR)DSS}$; identical low side and high side switch with identical R_G

3 Electrical characteristics

Table 4 Static characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|---|---------------|--------|------|------|----------|---|
| | | Min. | Typ. | Max. | | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | 700 | - | - | V | $V_{GS}=0V, I_D=1mA$ |
| Gate threshold voltage | $V_{(GS)th}$ | 2.50 | 3 | 3.50 | V | $V_{DS}=V_{GS}, I_D=0.09mA$ |
| Zero gate voltage drain current | I_{DSS} | - | - | 1 | μA | $V_{DS}=700V, V_{GS}=0V, T_j=25^\circ C$ $V_{DS}=700V, V_{GS}=0V, T_j=150^\circ C$ |
| Gate-source leakage current incl. Zener diode | I_{GSS} | - | - | 1 | μA | $V_{GS}=20V, V_{DS}=0V$ |
| Drain-source on-state resistance | $R_{DS(on)}$ | - | 0.49 | 0.60 | Ω | $V_{GS}=10V, I_D=1.8A, T_j=25^\circ C$ $V_{GS}=10V, I_D=1.8A, T_j=150^\circ C$ |
| Gate resistance | R_G | - | 10 | - | Ω | $f=1\text{ MHz, open drain}$ |

Table 5 Dynamic characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--|--------------|--------|------|------|------|---|
| | | Min. | Typ. | Max. | | |
| Input capacitance | C_{iss} | - | 364 | - | pF | $V_{GS}=0V, V_{DS}=400V, f=250kHz$ |
| Output capacitance | C_{oss} | - | 7 | - | pF | $V_{GS}=0V, V_{DS}=400V, f=250kHz$ |
| Effective output capacitance, energy related ¹⁾ | $C_{o(er)}$ | - | 17 | - | pF | $V_{GS}=0V, V_{DS}=0...400V$ |
| Effective output capacitance, time related ²⁾ | $C_{o(tr)}$ | - | 200 | - | pF | $I_D=constant, V_{GS}=0V, V_{DS}=0...400V$ |
| Turn-on delay time | $t_{d(on)}$ | - | 14 | - | ns | $V_{DD}=400V, V_{GS}=13V, I_D=1.4A,$ $R_G=5.3\Omega$ |
| Rise time | t_r | - | 5.5 | - | ns | $V_{DD}=400V, V_{GS}=13V, I_D=1.4A,$ $R_G=5.3\Omega$ |
| Turn-off delay time | $t_{d(off)}$ | - | 63 | - | ns | $V_{DD}=400V, V_{GS}=13V, I_D=1.4A,$ $R_G=5.3\Omega$ |
| Fall time | t_f | - | 23 | - | ns | $V_{DD}=400V, V_{GS}=13V, I_D=1.4A,$ $R_G=5.3\Omega$ |

Table 6 Gate charge characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-----------------------|---------------|--------|------|------|------|---|
| | | Min. | Typ. | Max. | | |
| Gate to source charge | Q_{gs} | - | 1.6 | - | nC | $V_{DD}=400V, I_D=1.4A, V_{GS}=0\text{ to }10V$ |
| Gate to drain charge | Q_{gd} | - | 3.7 | - | nC | $V_{DD}=400V, I_D=1.4A, V_{GS}=0\text{ to }10V$ |
| Gate charge total | Q_g | - | 10.5 | - | nC | $V_{DD}=400V, I_D=1.4A, V_{GS}=0\text{ to }10V$ |
| Gate plateau voltage | $V_{plateau}$ | - | 4.4 | - | V | $V_{DD}=400V, I_D=1.4A, V_{GS}=0\text{ to }10V$ |

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

Table 7 Reverse diode characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-------------------------------|-----------|--------|------|------|---------|---|
| | | Min. | Typ. | Max. | | |
| Diode forward voltage | V_{SD} | - | 0.9 | - | V | $V_{GS}=0V, I_F=2.5A, T_j=25^{\circ}C$ |
| Reverse recovery time | t_{rr} | - | 190 | - | ns | $V_R=400V, I_F=1.4A, di_F/dt=50A/\mu s$ |
| Reverse recovery charge | Q_{rr} | - | 0.8 | - | μC | $V_R=400V, I_F=1.4A, di_F/dt=50A/\mu s$ |
| Peak reverse recovery current | I_{rrm} | - | 9 | - | A | $V_R=400V, I_F=1.4A, di_F/dt=50A/\mu s$ |

4 Electrical characteristics diagrams

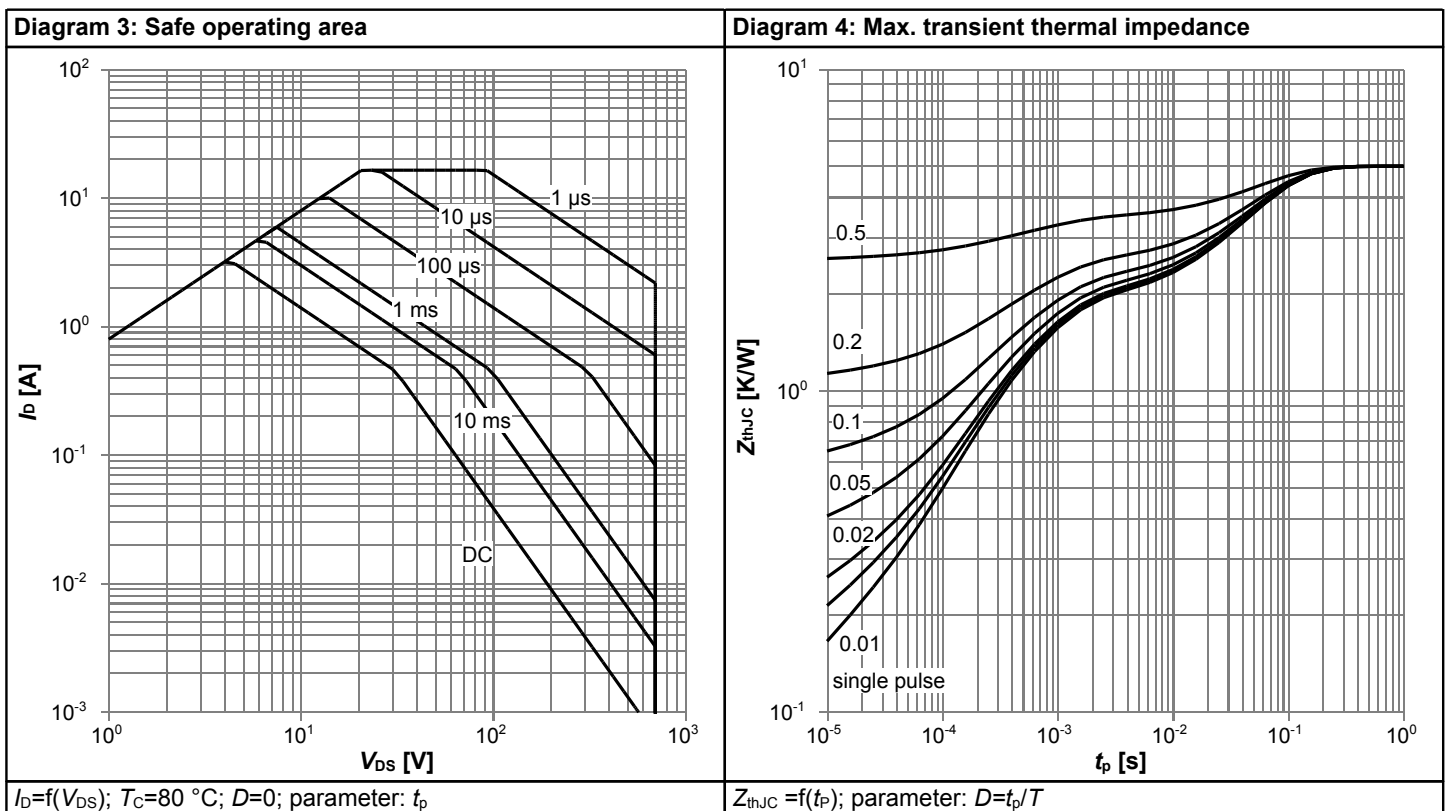
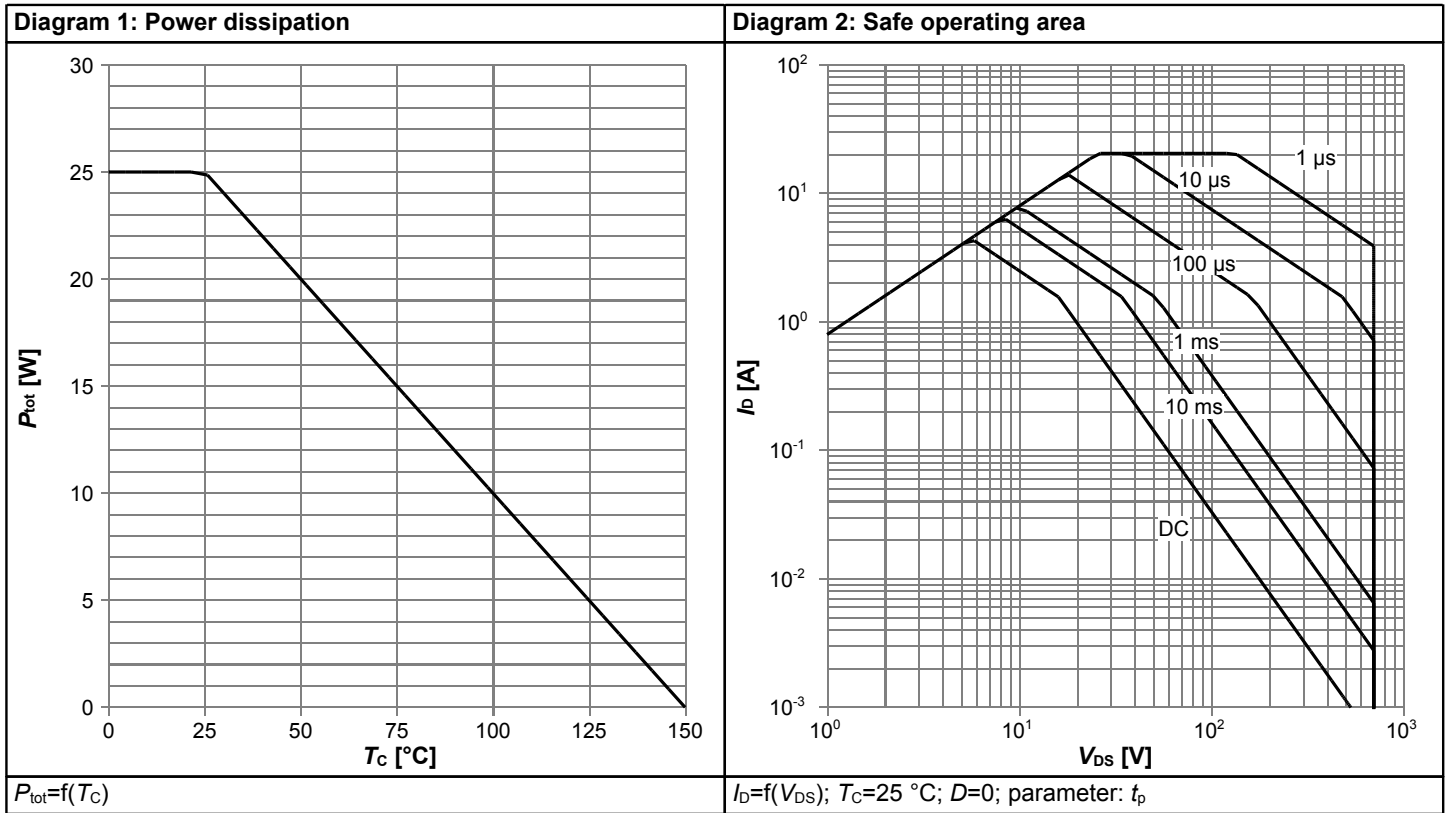
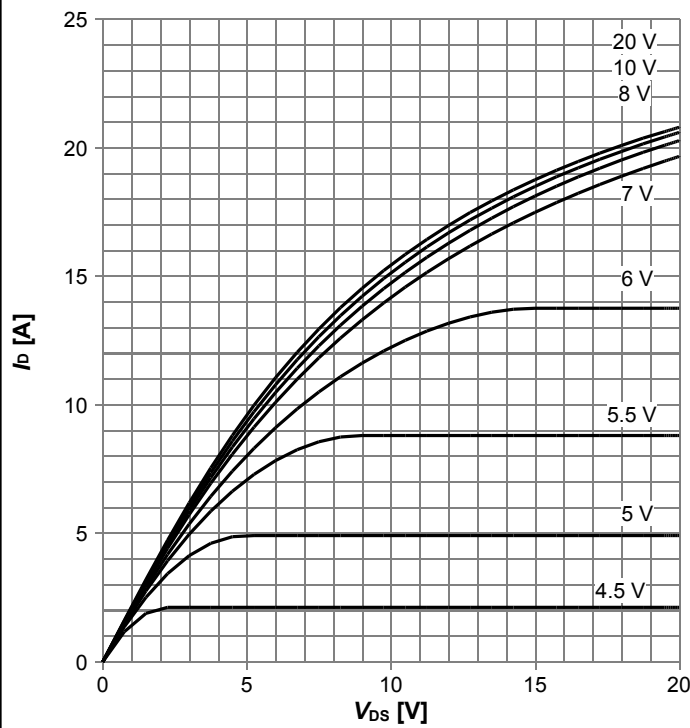
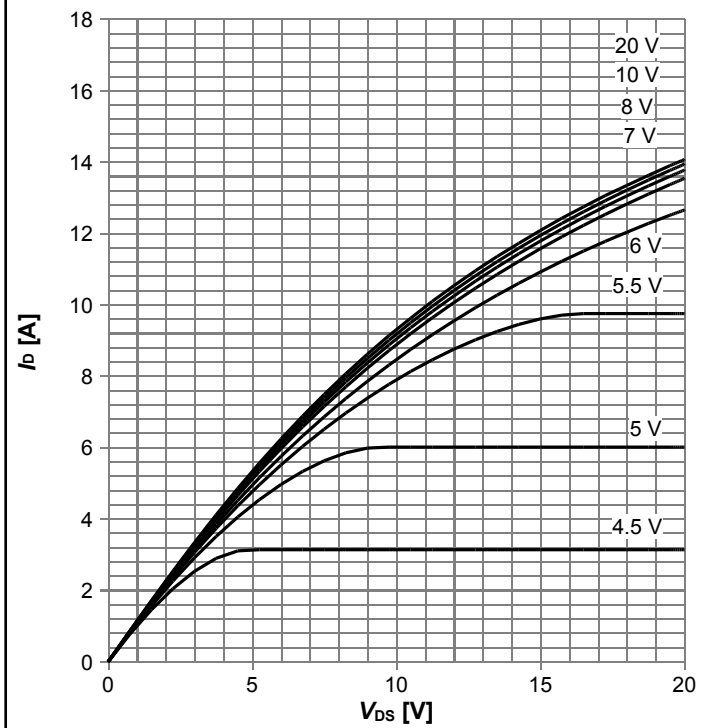


Diagram 5: Typ. output characteristics



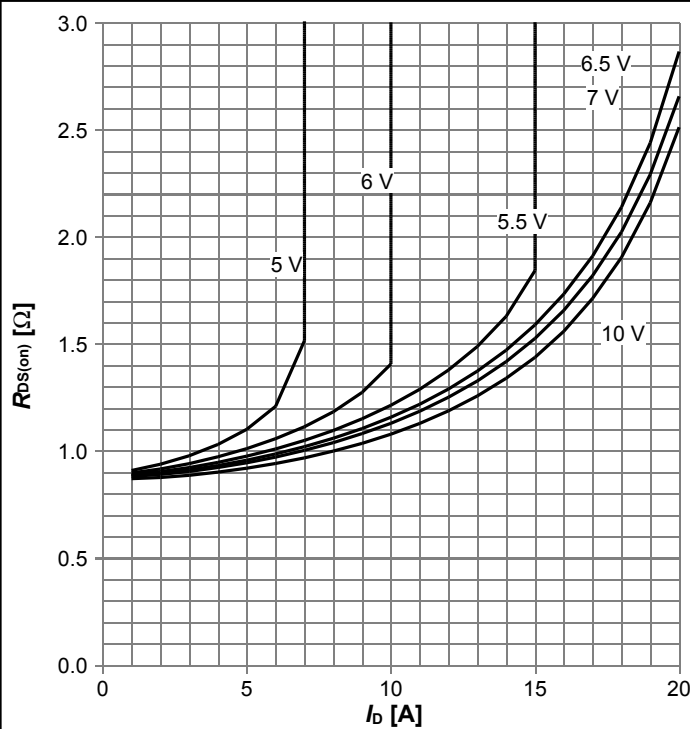
$I_D=f(V_{DS}); T_j=25\text{ °C};$ parameter: V_{GS}

Diagram 6: Typ. output characteristics



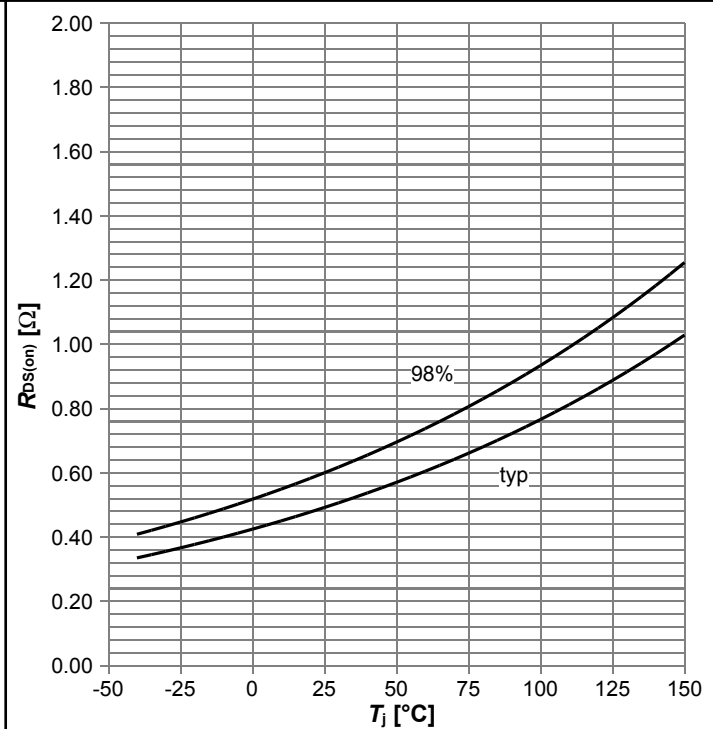
$I_D=f(V_{DS}); T_j=125\text{ °C};$ parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



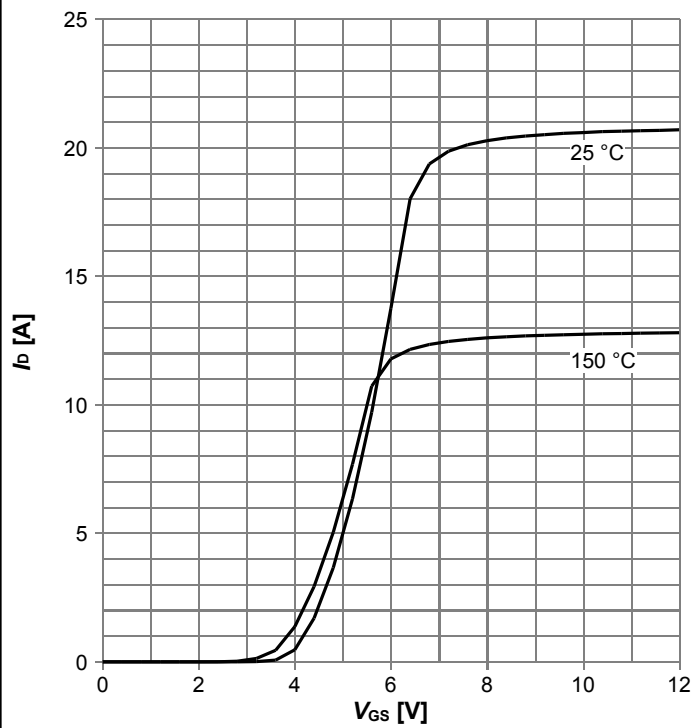
$R_{DS(on)}=f(I_D); T_j=125\text{ °C};$ parameter: V_{GS}

Diagram 8: Drain-source on-state resistance



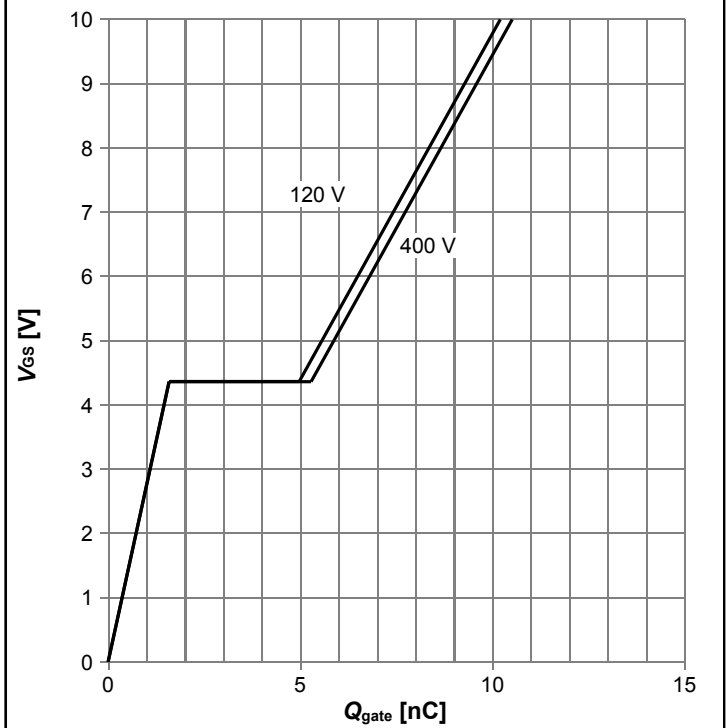
$R_{DS(on)}=f(T_j); I_D=1.8\text{ A}; V_{GS}=10\text{ V}$

Diagram 9: Typ. transfer characteristics



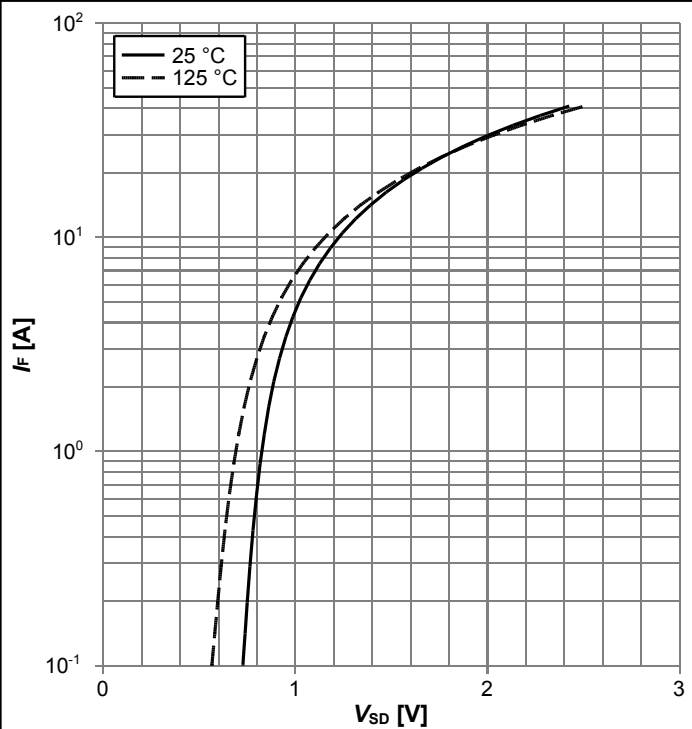
$I_D = f(V_{GS})$; $V_{DS} = 20V$; parameter: T_j

Diagram 10: Typ. gate charge



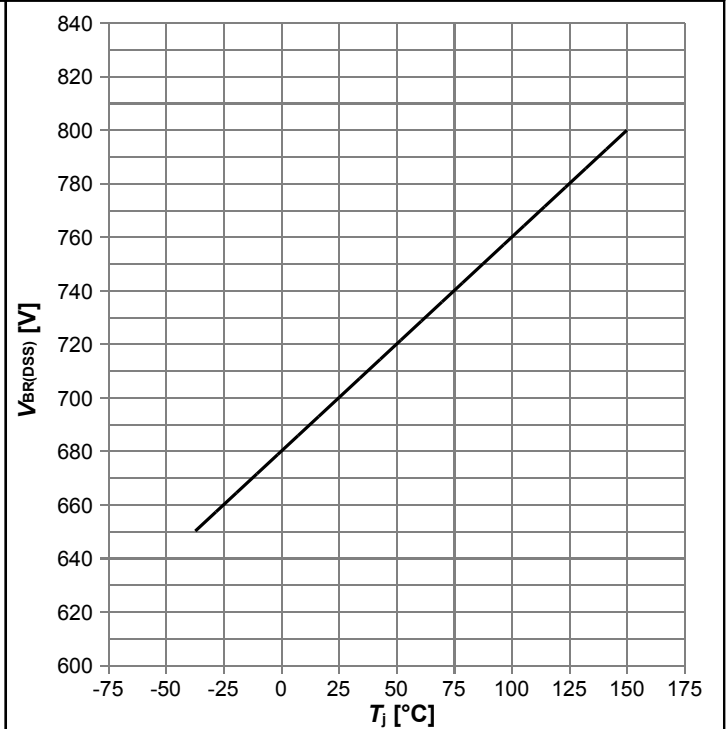
$V_{GS} = f(Q_{gate})$; $I_D = 1.4 A$ pulsed; parameter: V_{DD}

Diagram 11: Forward characteristics of reverse diode



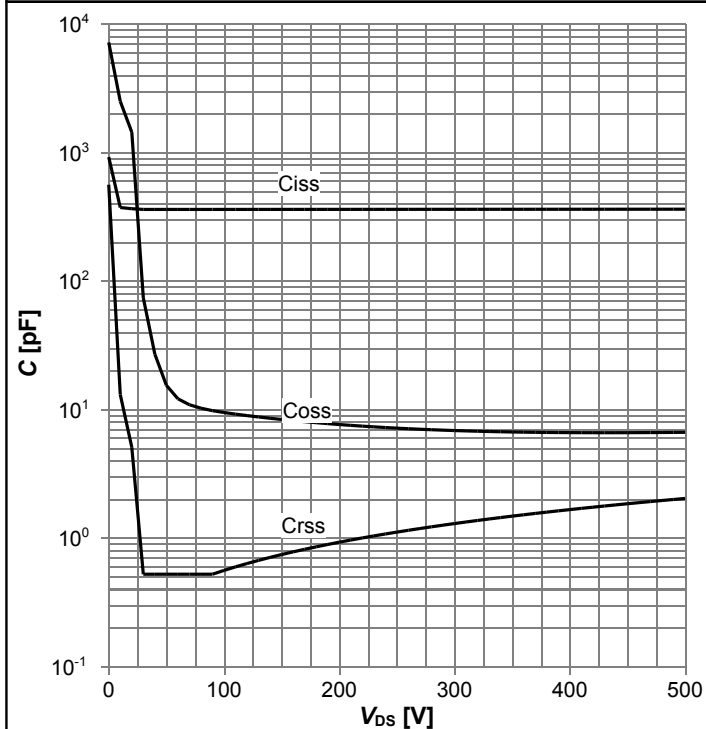
$I_F = f(V_{SD})$; parameter: T_j

Diagram 13: Drain-source breakdown voltage



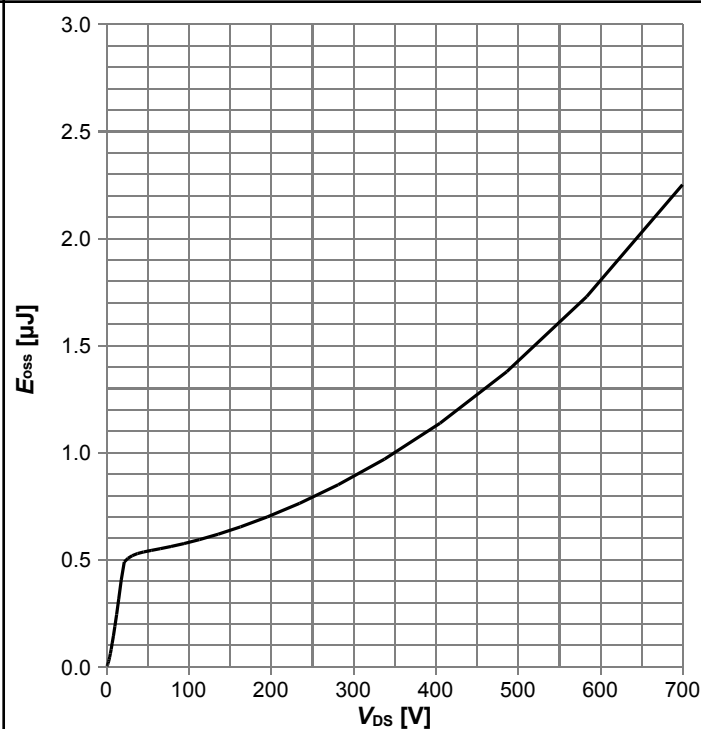
$V_{BR(DSS)} = f(T_j)$; $I_D = 1 mA$

Diagram 14: Typ. capacitances



$C=f(V_{DS}); V_{GS}=0\text{ V}; f=250\text{ kHz}$

Diagram 15: Typ. Coss stored energy



$E_{oss}=f(V_{DS})$

5 Test Circuits

Table 8 Diode characteristics

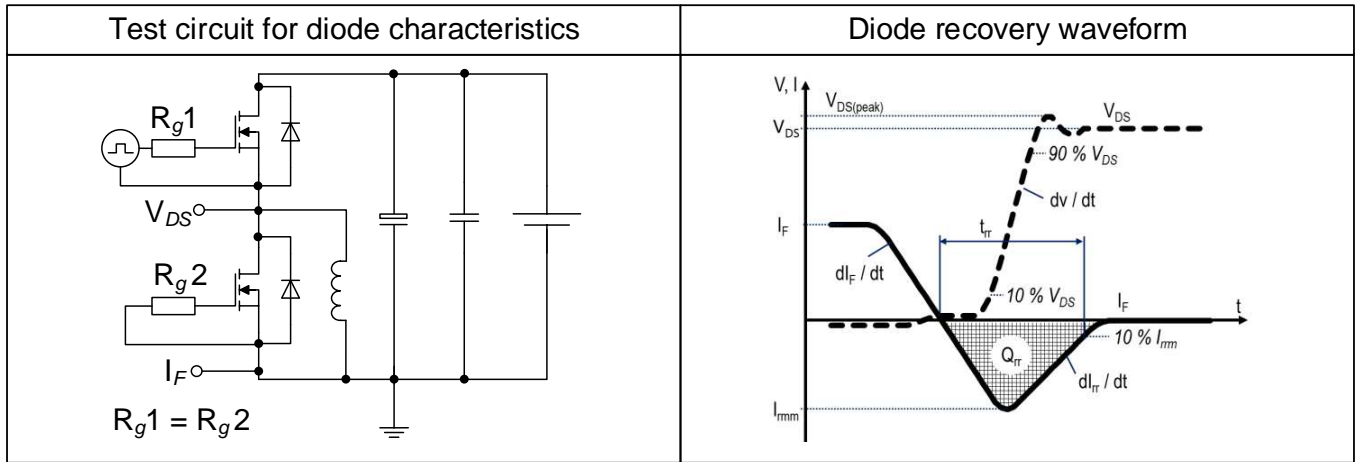


Table 9 Switching times

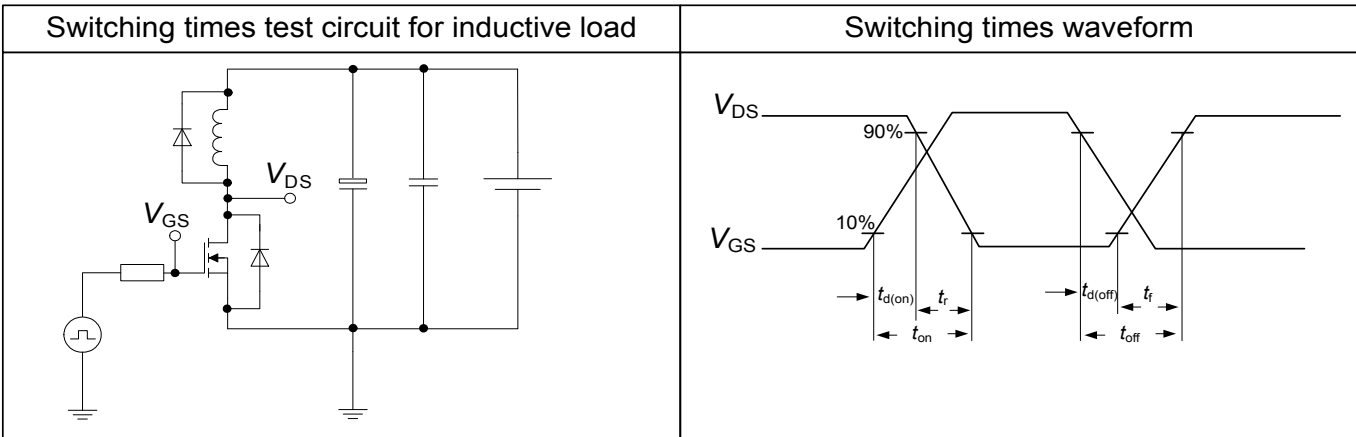
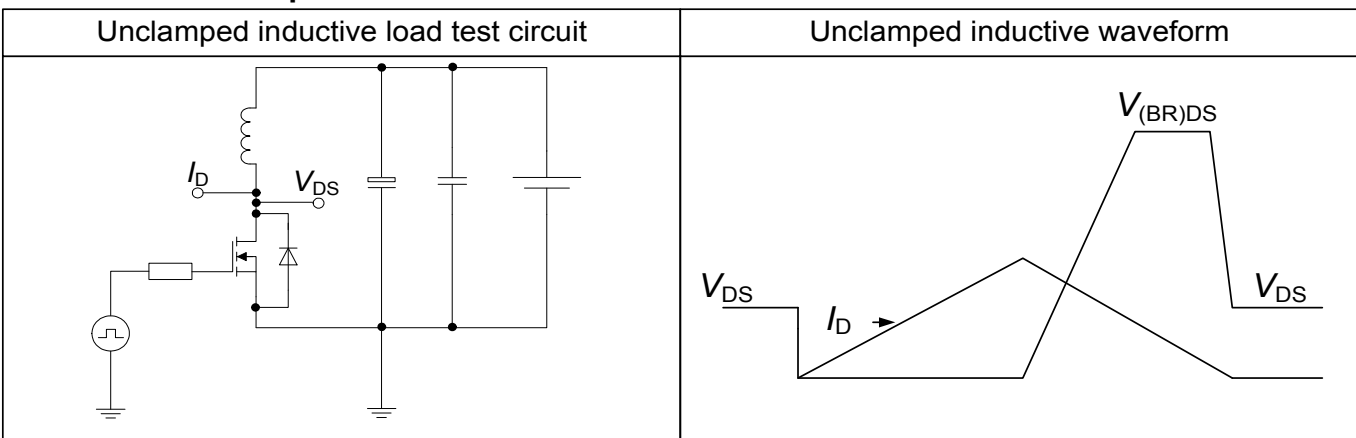
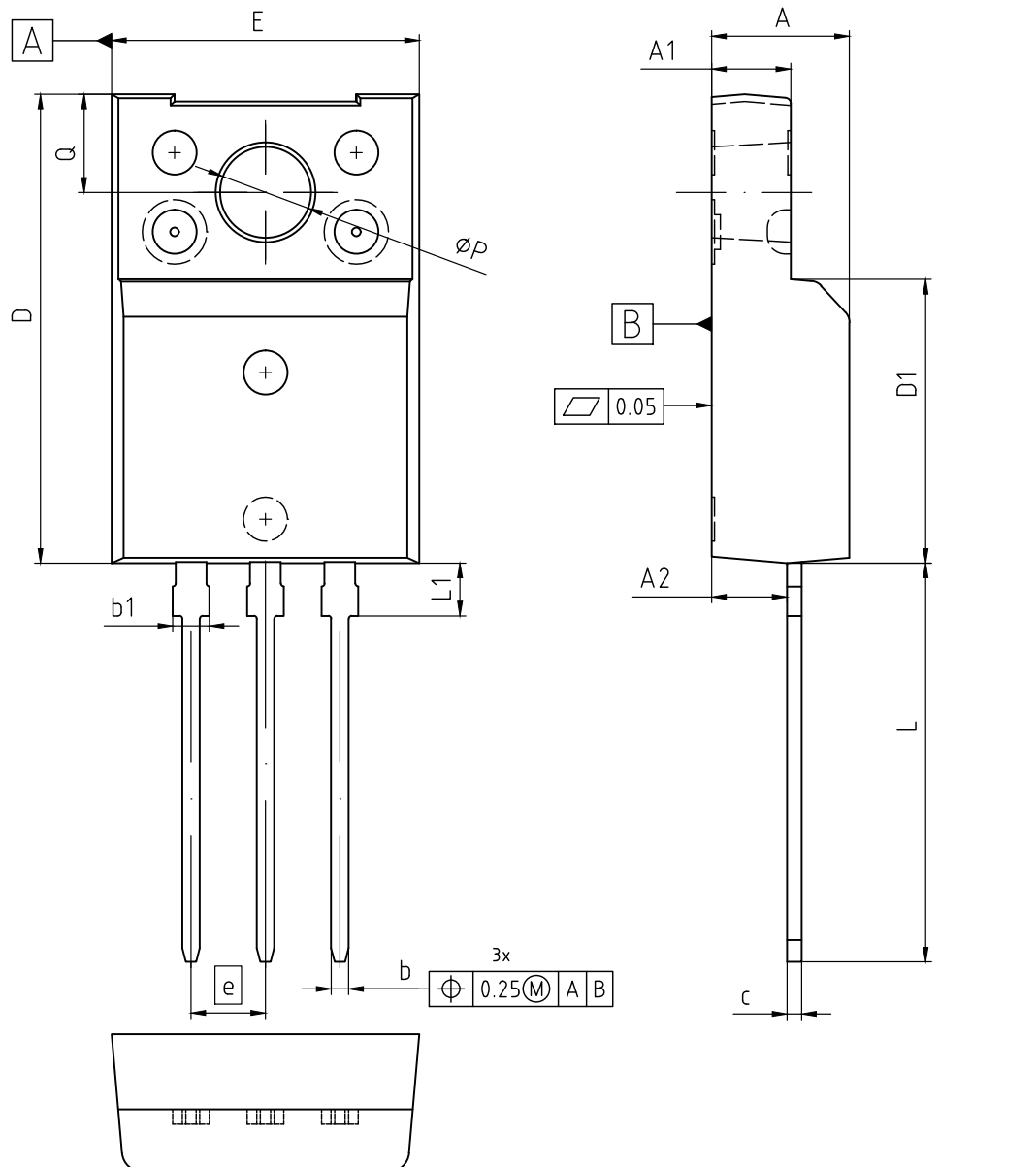


Table 10 Unclamped inductive load



6 Package Outlines



| DIMENSIONS | MILLIMETERS | |
|------------|-------------|-------|
| | MIN. | MAX. |
| A | 4.60 | 4.80 |
| A1 | 2.60 | 2.80 |
| A2 | 2.47 | 2.67 |
| b | 0.56 | 0.69 |
| b1 | 1.01 | 1.15 |
| c | 0.46 | 0.59 |
| D | 15.90 | 16.10 |
| D1 | 9.58 | 9.78 |
| E | 10.40 | 10.60 |
| e | | 2.54 |
| N | | 3 |
| L | 13.45 | 13.75 |
| L1 | 1.70 | 1.90 |
| ØP | 3.00 | 3.20 |
| Q | 3.25 | 3.45 |

NOTES:
 ALL DIMENSIONS DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.
 ALL DIMENSIONS REFER TO JEDEC STANDARD TO-281

| |
|------------------------------------|
| DOCUMENT NO. Z8B00180155 |
| REVISION 04 |
| SCALE 5:1 0 1 2 3 4 5mm |
| EUROPEAN PROJECTION |
| ISSUE DATE 07.11.2016 |

Figure 1 Outline PG-TO 220 FullPAK - Narrow Lead, dimensions in mm - Industrial Grade

7 Appendix A

Table 11 Related Links

- **IFX CoolMOS™ P7 Webpage:** www.infineon.com
- **IFX Design tools:** www.infineon.com

Revision History

IPAN70R600P7S

Revision: 2018-02-13, Rev. 2.1

Previous Revision

| Revision | Date | Subjects (major changes since last revision) |
|----------|------------|--|
| 2.0 | 2017-02-16 | Release of final version |
| 2.1 | 2018-02-13 | Corrected front page text |

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